

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L6	3198	bump near5 electrode	USPAT	OR	ON	2005/03/20 19:10
L7	5508	bump near5 electrode	US-PGPU B; USPAT; USOCR	OR	ON	2005/03/20 20:48
L8	4172	7 and (insulat\$3 dielectric)	US-PGPU B; USPAT; USOCR	OR	ON	2005/03/20 20:49
L9	3618	8 and (etch\$3 pattern\$3)	US-PGPU B; USPAT; USOCR	OR	ON	2005/03/20 20:48
L10	3028	9 and wir\$3	US-PGPU B; USPAT; USOCR	OR	ON	2005/03/20 20:49
L13	10304	bump near5 electrode	EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2005/03/20 20:48
L14	1950	13 and (etch\$3 pattern\$3)	EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2005/03/20 20:48
L15	628	14 and (insulat\$3 dielectric)	EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2005/03/20 20:49
L16	288	15 and wir\$3	EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2005/03/20 20:49

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L3	43880	(257/600-798).CCLS.	US-PGPU B; USPAT; USOCR	OR	OFF	2005/03/20 17:11
L4	13561	3 and (first near5 (metal conductive))	US-PGPU B; USPAT; USOCR	OR	ON	2005/03/20 17:12
L5	12343	3 and (second near5 (metal conductive))	US-PGPU B; USPAT; USOCR	OR	ON	2005/03/20 17:12
L6	3860	3 and (third near5 (metal conductive))	US-PGPU B; USPAT; USOCR	OR	ON	2005/03/20 17:12
L7	10587	3 and 4 and 5	US-PGPU B; USPAT; USOCR	OR	ON	2005/03/20 15:59
L8	4782	7 and (inuslat\$3 dielectric)	US-PGPU B; USPAT; USOCR	OR	ON	2005/03/20 17:13
L9	4289	8 and (etch\$3 pattern\$3)	US-PGPU B; USPAT; USOCR	OR	ON	2005/03/20 17:14
L10	2555	9 and wir\$3	US-PGPU B; USPAT; USOCR	OR	ON	2005/03/20 16:02
L11	1125	10 and (resin (encapsulate encapsulating Encapsulant))	US-PGPU B; USPAT; USOCR	OR	ON	2005/03/20 16:06
L12	9261	(438/106-127).CCLS.	US-PGPU B; USPAT; USOCR	OR	OFF	2005/03/20 17:12
L13	2738	(438/612-617).CCLS.	US-PGPU B; USPAT; USOCR	OR	OFF	2005/03/20 17:12
L14	11554	12 13v	US-PGPU B; USPAT; USOCR	OR	ON	2005/03/20 17:12
L15	2816	14 and (first near5 (metal conductive))	US-PGPU B; USPAT; USOCR	OR	ON	2005/03/20 18:41
L16	2501	14 and (second near5 (metal conductive))	US-PGPU B; USPAT; USOCR	OR	ON	2005/03/20 17:12
L17	651	14 and (third near5 (metal conductive))	US-PGPU B; USPAT; USOCR	OR	ON	2005/03/20 17:13

L18	529	15 and 16 and 17	US-PGPU B; USPAT; USOCR	OR	ON	2005/03/20 17:13
L19	220	18 and (insulat\$3 dielectric)	US-PGPU B; USPAT; USOCR	OR	ON	2005/03/20 17:13
L20	417	18 and (insulat\$3 dielectric)	US-PGPU B; USPAT; USOCR	OR	ON	2005/03/20 17:13
L21	363	20 and (etch\$3 pattern\$3)	US-PGPU B; USPAT; USOCR	OR	ON	2005/03/20 17:14
L22	60076	laminat\$3 near5 (plate metal conductor conductive)	US-PGPU B; USPAT; USOCR	OR	ON	2005/03/20 18:41
L23	29990	22 and (etch\$3 pattern\$3)	US-PGPU B; USPAT; USOCR	OR	ON	2005/03/20 17:41
L24	10183	23 and (insulat\$3 dielectric)	US-PGPU B; USPAT; USOCR	OR	ON	2005/03/20 18:42
L25	5683	24 and resin	US-PGPU B; USPAT; USOCR	OR	ON	2005/03/20 17:42
L26	5175	25 and (substrate chip die semiconductor)	US-PGPU B; USPAT; USOCR	OR	ON	2005/03/20 17:43
L27	4564	26 and (via hole open\$3)	US-PGPU B; USPAT; USOCR	OR	ON	2005/03/20 17:43
L28	4197	27 and (electrode wire bond\$3)	US-PGPU B; USPAT; USOCR	OR	ON	2005/03/20 17:45
L29	3734	28 and (copper Cu gold Au silver Ag)	US-PGPU B; USPAT; USOCR	OR	ON	2005/03/20 18:15
L31	150805	laminat\$3 and (plate metal conductor conductive)	EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2005/03/20 18:41
L32	3887	31 and (first near5 (metal conductive))	EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2005/03/20 18:41
L33	3660	31 and (second near5 (metal conductive))	EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2005/03/20 18:41

<b>L34</b>	<b>569</b>	<b>31 and (third near5 (metal conductive))</b>	<b>EPO; JPO; DERWENT ; IBM_TDB</b>	<b>OR</b>	<b>ON</b>	<b>2005/03/20 18:42</b>
<b>L35</b>	<b>339</b>	<b>32 and 33 and 34</b>	<b>EPO; JPO; DERWENT ; IBM_TDB</b>	<b>OR</b>	<b>ON</b>	<b>2005/03/20 18:42</b>
<b>L36</b>	<b>27</b>	<b>35 and (inuslat\$3 dielectric)</b>	<b>EPO; JPO; DERWENT ; IBM_TDB</b>	<b>OR</b>	<b>ON</b>	<b>2005/03/20 18:42</b>